

TOSHIBA HIGH EFFICIENCY DIODE STACK (HED) SILICON EPITAXIAL TYPE

20DL2CZ47A, 20FL2CZ47A

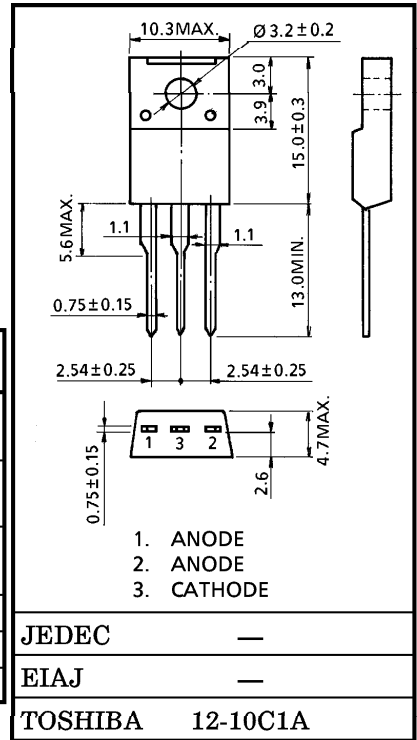
SWITCHING TYPE POWER SUPPLY APPLICATION
CONVERTER & CHOPPER APPLICATION

Unit in mm

- Repetitive Peak Reverse Voltage : $V_{RRM}=200, 300V$
- Average Output Rectified Current : $I_O=20A$
- Ultra Fast Reverse-Recovery Time : $t_{rr}=35ns$ (Max.)
- Low Switching Losses and Low Output Noise.

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Reverse Voltage	V_{RRM}	200	V
		300	
Average Output Rectified Current (Full Sine Waveform)	I_O	20	A
Peak One Cycle Surge Forward Current (Non-Repetitive)	I_{FSM}	100 (50Hz)	A
		110 (60Hz)	
Junction Temperature	T_j	-40~150	$^\circ C$
Storage Temperature Range	T_{stg}	-40~150	$^\circ C$
Screw Torque	—	0.6	N·m



ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

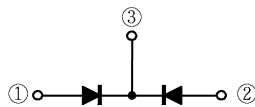
Weight : 2.0g

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage (Note 1)	V_{FM}	$I_{FM}=10A$	—	—	0.98	V
			—	—	1.3	
Repetitive Peak Reverse Current (Note 1)	I_{RRM}	$V_{RRM}=\text{Rated}$	—	—	50	μA
Reverse Recovery Time (Note 1)	t_{rr}	$I_F=2.0A, di/dt=-50A/\mu s$	—	—	35	ns
Forward Recovery Time (Note 1)	t_{fr}	$I_F=1.0A$	—	—	100	ns
Thermal Resistance	$R_{th(j-c)}$	DC Total, Junction to Case	—	—	3.0	$^\circ C/W$

(Note 1) A value of one cell.

POLARITY

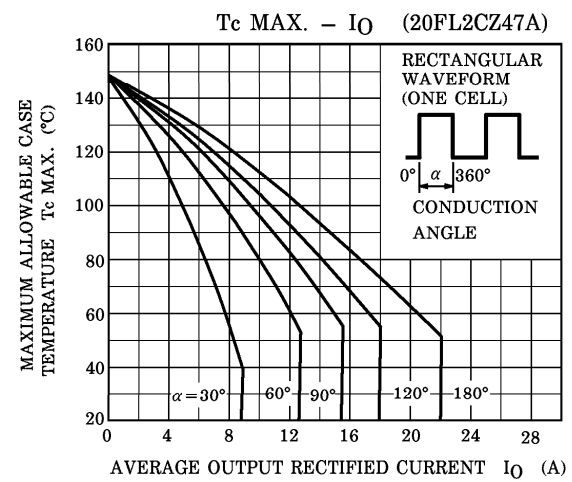
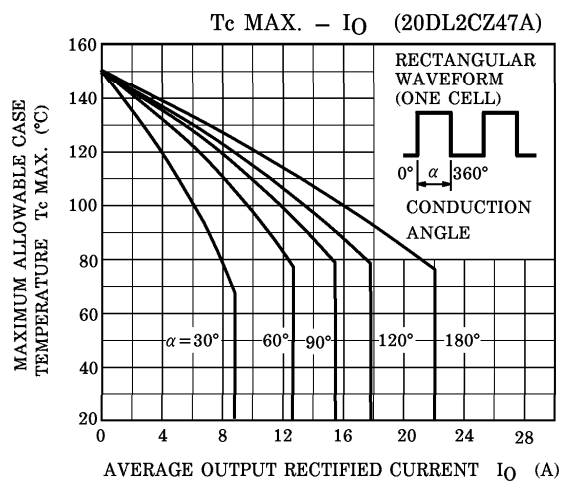
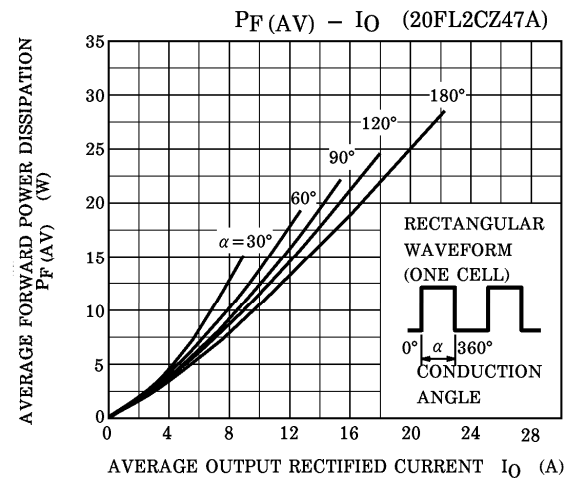
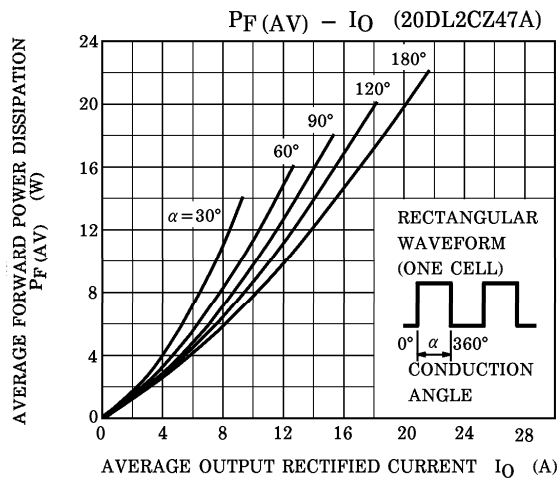
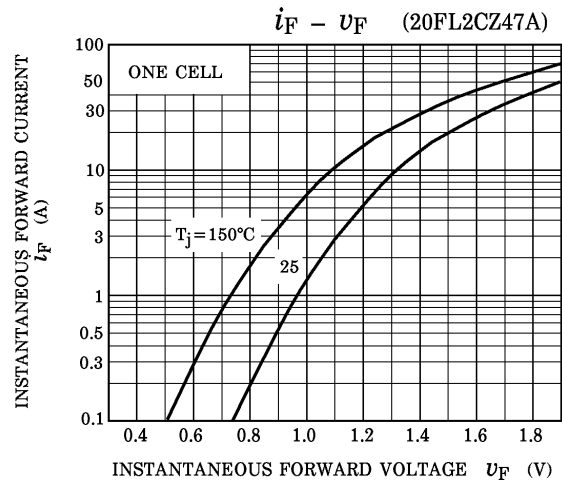
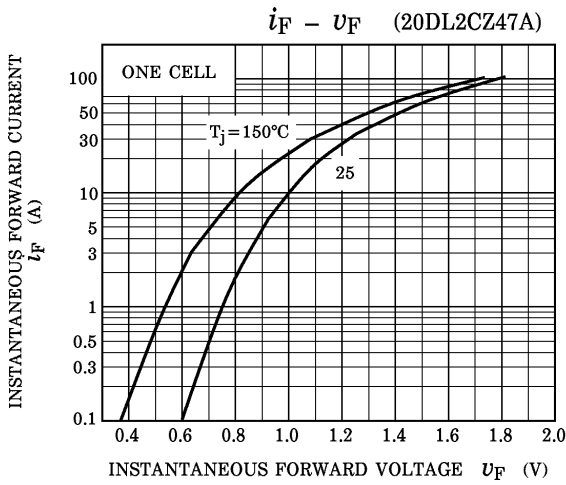
MARKING



*1	MARK	20DL2CZ 20FL2CZ	TYPE	20DL2CZ47A 20FL2CZ47A
*2	A Lot Number			
*3	<div style="display: flex; align-items: center;"> <div style="border: 1px solid black; width: 15px; height: 15px; margin-right: 5px;"></div> <div style="border: 1px solid black; width: 15px; height: 15px; margin-right: 5px; margin-left: 10px;"></div> Month (Starting from Alphabet A) </div> <div style="display: flex; align-items: center; margin-top: 5px;"> <div style="border-bottom: 1px solid black; width: 20px; margin-right: 5px;"></div> Year (Last Number of the Christian Era) </div>			

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